

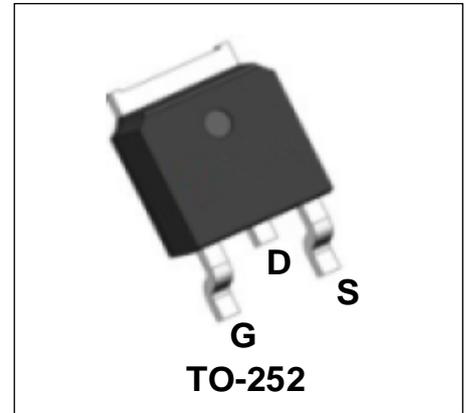
## 40V P-Channel Enhancement Mode Power MOSFET

### Description

WMO50P04T1 uses advanced power trench technology that has been especially tailored to minimize the on-state resistance and yet maintain superior switching performance.

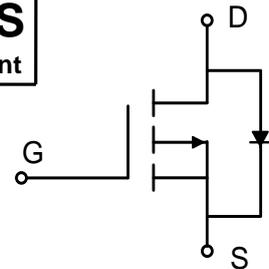
### Features

- $V_{DS} = -40V$ ,  $I_D = -50A$   
 $R_{DS(on)} < 13m\Omega$  @  $V_{GS} = -10V$   
 $R_{DS(on)} < 20m\Omega$  @  $V_{GS} = -4.5V$
- Green Device Available
- Low Gate Charge
- Advanced High Cell Density Trench Technology
- 100% EAS Guaranteed



### Applications

- Power Management Switches
- DC/DC Converters



### Absolute Maximum Ratings

Parameter		Symbol	Value	Unit
Drain-Source Voltage		$V_{DS}$	-40	V
Gate-Source Voltage		$V_{GS}$	$\pm 20$	V
Continuous Drain Current@-10V <sup>1</sup>	$T_C=25^\circ C$	$I_D$	-50	A
	$T_C=100^\circ C$		-31	
Pulsed Drain Current <sup>2</sup>		$I_{DM}$	-103	A
Single Pulse Avalanche Energy <sup>3</sup>		<b>EAS</b>	72	mJ
Avalanche Current		$I_{AS}$	-38	A
Total Power Dissipation <sup>4</sup>	$T_C=25^\circ C$	$P_D$	51	W
Operating Junction and Storage Temperature Range		$T_J, T_{STG}$	-55 to 150	$^\circ C$

### Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance from Junction-to-Ambient <sup>1</sup>	$R_{\theta JA}$	62.5	$^\circ C/W$
Thermal Resistance from Junction-to-Case <sup>1</sup>	$R_{\theta JC}$	2.45	$^\circ C/W$

**Electrical Characteristics**  $T_c = 25^\circ\text{C}$ , unless otherwise noted

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
<b>Static Characteristics</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-40	-	-	V
Gate-body Leakage current	$I_{GSS}$	$V_{DS} = 0V, V_{GS} = \pm 20V$	-	-	$\pm 100$	nA
Zero Gate Voltage Drain Current	$T_J=25^\circ\text{C}$	$V_{DS} = -32V, V_{GS} = 0V$	-	-	1	$\mu A$
	$T_J=55^\circ\text{C}$		-	-	5	
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-1.0	-1.6	-2.5	V
Drain-Source On-Resistance <sup>2</sup>	$R_{DS(on)}$	$V_{GS} = -10V, I_D = -16A$	-	11.5	13	m $\Omega$
		$V_{GS} = -4.5V, I_D = -12A$	-	16	20	
Forward Transconductance <sup>2</sup>	$g_{fs}$	$V_{DS} = -5V, I_D = -18A$	-	23	-	S
<b>Dynamic Characteristics</b>						
Input Capacitance	$C_{iss}$	$V_{DS} = -20V, V_{GS} = 0V, f = 1MHz$	-	3320	-	pF
Output Capacitance	$C_{oss}$		-	290	-	
Reverse Transfer Capacitance	$C_{rss}$		-	225	-	
<b>Switching Characteristics</b>						
Gate Resistance	$R_g$	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$	-	3.3	-	$\Omega$
Total Gate Charge	$Q_g$	$V_{GS} = -4.5V, V_{DS} = -20V, I_D = -12A$	-	28	-	nC
Gate-Source Charge	$Q_{gs}$		-	7.8	-	
Gate-Drain Charge	$Q_{gd}$		-	7.6	-	
Turn-on Delay Time	$t_{d(on)}$	$V_{GS} = -10V, V_{DS} = -15V, R_g = 3.3\Omega, I_D = -1A$	-	41	-	nS
Rise Time	$t_r$		-	35.5	-	
Turn-off Delay Time	$t_{d(off)}$		-	99	-	
Fall Time	$t_f$		-	9.5	-	
<b>Drain-Source Body Diode Characteristics</b>						
Diode Forward Voltage <sup>2</sup>	$V_{SD}$	$I_S = -1A, V_{GS} = 0V$	-	-	-1	V
Continuous Source Current <sup>1,5</sup>	$I_S$	$V_G = V_D = 0V$ , Force Current	-	-	-50	A

## Notes:

- 1.The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width  $\leq 300\mu s$  , duty cycle  $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is  $V_{DD}=25V, V_{GS}=10V, L=0.1mH, I_{AS}=38A$
- 4.The power dissipation is limited by 150 $^\circ\text{C}$  junction temperature
- 5.The data is theoretically the same as  $I_D$  and  $I_{DM}$  , in real applications , should be limited by total power dissipation.

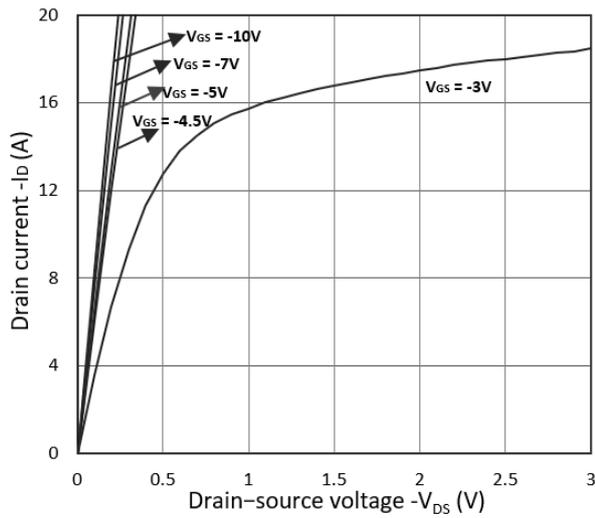


Figure 1. Output Characteristics

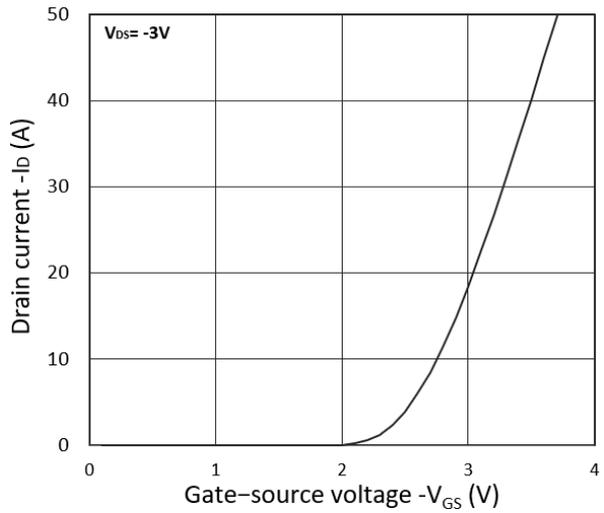


Figure 2. Transfer Characteristics

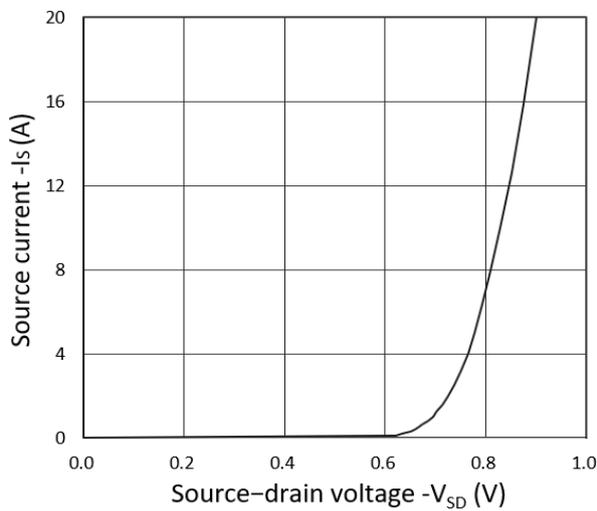


Figure 3. Forward Characteristics of Reverse

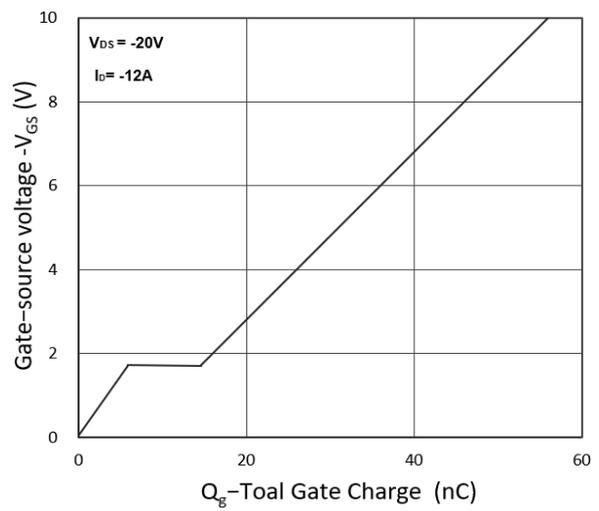


Figure 4. Gate Charge Characteristics

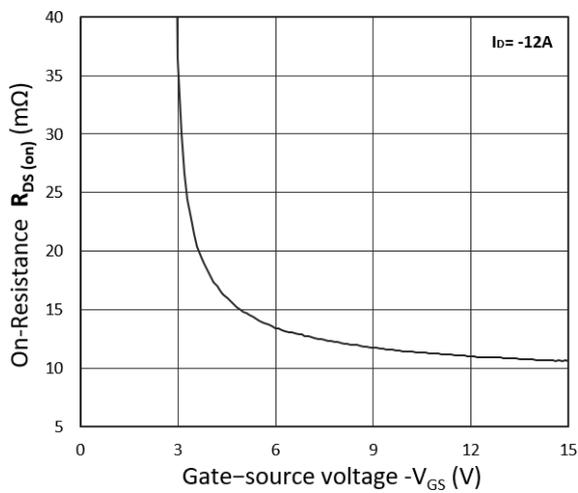


Figure 5.  $R_{DS(on)}$  vs.  $V_{GS}$

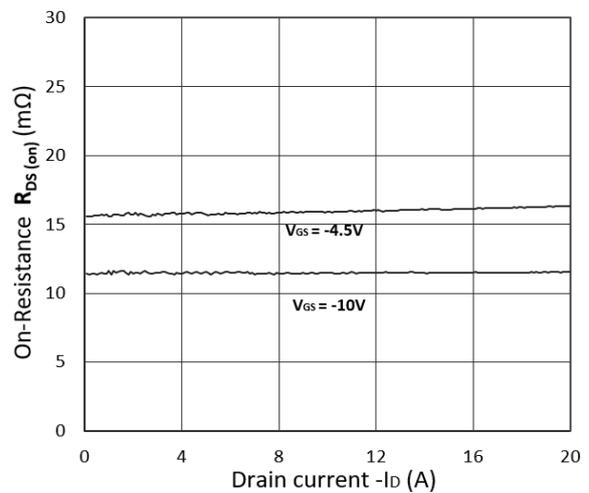


Figure 6.  $R_{DS(on)}$  vs.  $I_D$

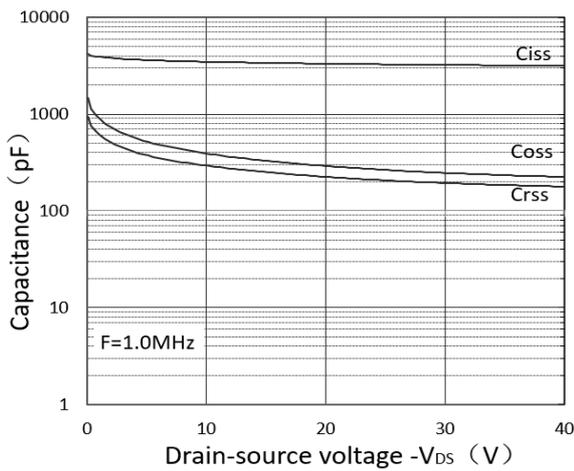


Figure 7. Capacitance Characteristics

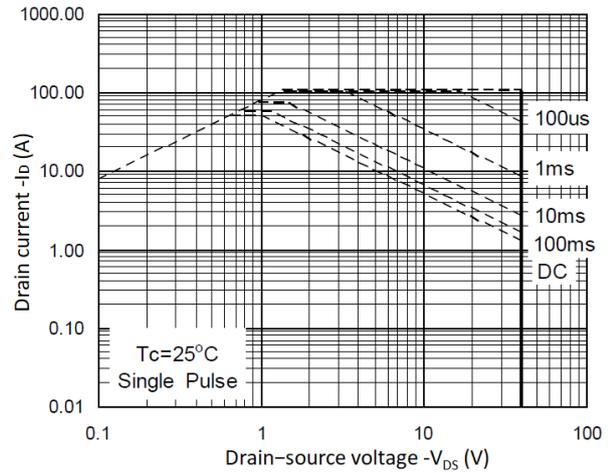


Figure 8. Safe Operating Area

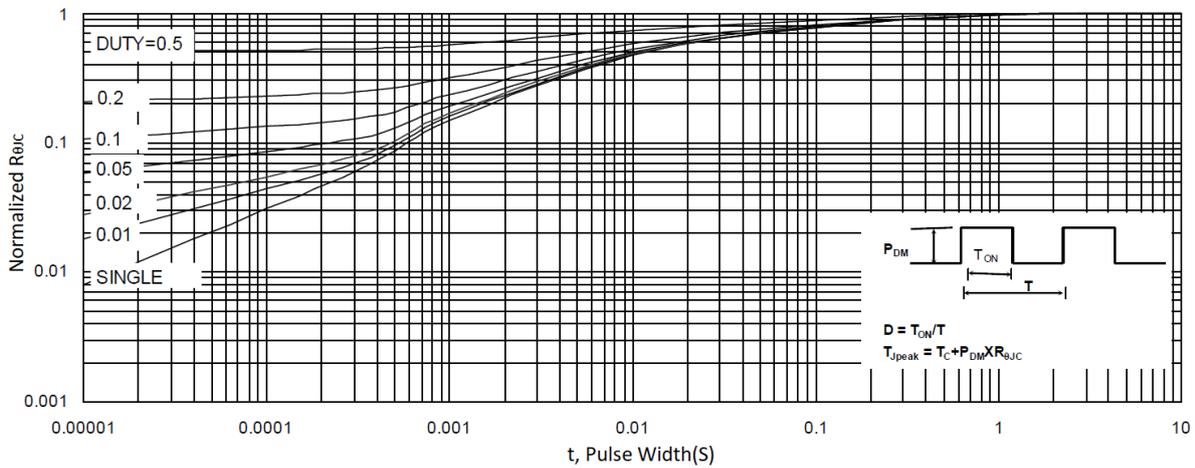


Figure 9. Normalized Maximum Transient Thermal Impedance

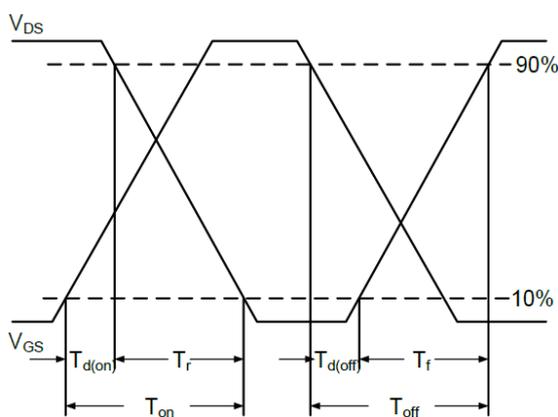


Figure 10. Switching Time Waveform

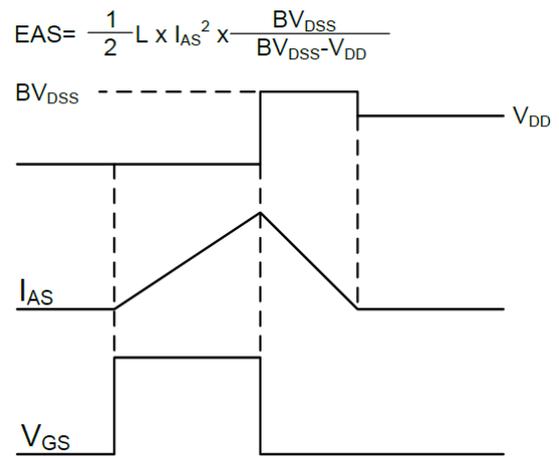
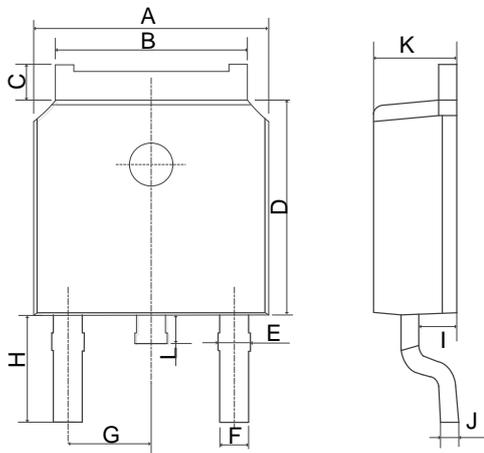


Figure 11. Unclamped Inductive Switching Waveform

$$EAS = \frac{1}{2} L \times I_{AS}^2 \times \frac{BV_{DSS}}{BV_{DSS} - V_{DD}}$$

## Mechanical Dimensions for TO-252



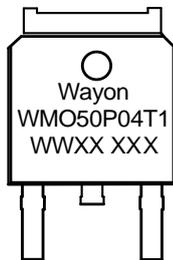
## COMMON DIMENSIONS

SYMBOL	MM	
	MIN	MAX
A	6.40	6.80
B	5.13	5.50
C	0.88	1.28
D	5.90	6.22
E	0.68	1.10
F	0.68	0.91
G	2.29REF	
H	2.90REF	
I	0.85	1.17
J	0.51REF	
K	2.10	2.50
L	0.40	1.00

## Ordering Information

Part	Package	Marking	Packing method
WMO50P04T1	TO-252	WMO50P04T1	Tape and Reel

## Marking Information



WMO50P04T1 = Device code

WWXX XXX= Manufacturing code

## Contact Information

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